

**Claim Amendments:**

Claims 1-35 (Canceled)

36. (Original) A semiconductor processing component comprising silicon carbide, the component having a surface having an  $R_a$  less than about 2 microns, and an impurity content of less than about 1000 ppm along an outer portion of the component as measured by SIMS at a depth of 10 nm from the surface of the component.

37. (Original) The method of claim 36, wherein the component comprises a substrate and a silicon carbide coating thereon.

38. (Original) The method of claim 36, wherein the component is machined to have said  $R_a$  less than about 2 microns.

39. (Original) The method of claim 36, wherein said impurity content is less than about 500 ppm.

40. (Original) The method of claim 36, wherein said impurity content is less than about 200 ppm.

41. (Original) A semiconductor processing component for receiving a semiconductor wafer, the component having a surface having an  $R_a$  less than about 2 microns, and an impurity content of less than about 1000 ppm along an outer portion of the component, as measured by SIMS at depth of 10 nm from the surface.